LSF010x 1/2/8 Channel Auto-Bidirectional Multi-Voltage Level Translator for Open-Drain and Push-Pull Applications

1 Features

- Provides bidirectional voltage translation with no direction pin
- Supports up to 100-MHz up translation and greater than 100-MHz down translation at ≤ 30pF cap load and up To 40-MHz up/down translation at 50pF cap load
- Allows bidirectional voltage-level translation between
  - 0.95 V ↔ 1.8/2.5/3.3/5 V
  - 1.2 V ↔ 1.8/2.5/3.3/5 V
  - 1.8 V ↔ 2.5/3.3/5 V
  - 2.5 V ↔ 3.3/5 V
  - 3.3 V ↔ 5 V
- Low standby current
- 5-V tolerance I/O port to support TTL
- Low R_{ON} provides less signal distortion
- High-impedance I/O pins for EN = Low
- Flow-through pinout for easy PCB trace routing
- Latch-up performance >100 mA per JESD 17
- –40°C to 125°C Operating temperature range

2 Applications

- GPIO, MDIO, PMBus, SMBus, SDIO, UART, I²C, and other interfaces in telecom infrastructure
- Enterprise Systems
- Communications Equipment
- Personal Electronics
- Industrial Applications

3 Description

The LSF family of devices supports bidirectional voltage translation without the need for DIR pin which minimizes system effort (for PMBus, I²C, SMBus, etc.). The LSF family of devices supports up to 100-MHz up translation and greater than 100-MHz down translation at ≤ 30pF cap load and up to 40-MHz up/down translation at 50pF cap load which allows the LSF family to support more consumer or telecom interfaces (MDIO or SDIO).

LSF family supports 5-V tolerance on I/O port which makes it compatible with TTL levels in industrial and telecom applications. The LSF family is able to set up different voltage translation levels on each channel which makes it very flexible.

Device Information(1)

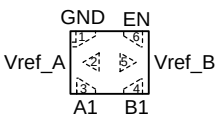
PART NUMBER	PACKAGE(PINS)	BODY SIZE (NOM)
LSF0101DRY	SON (6)	1.45 mm × 1.00 mm
LSF0101DTQ(2)	X2SON (6)	1.00 mm x 0.80 mm
LSF0102DQE	X2SON (8)	1.40 mm × 1.00 mm
LSF0102YZT	DSBGA (8)	1.90 mm × 1.00 mm
LSF0102DCT	SM8 (8)	2.80 mm × 2.95 mm
LSF0102DCU	VSSOP (8)	2.30 mm × 2.00 mm
LSF0108RKS	VQFN (20)	4.50 mm × 2.50 mm
LSF0108PW	TSSOP (20)	4.40 mm × 6.50 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

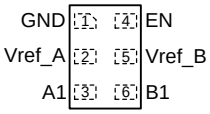
(2) Advance Information

LSF0101

DTQ Package
6-Pin X2SON
Transparent Top View

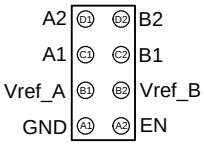


DRY Package
6-Pin SON
Transparent Top View

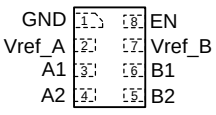


LSF0102

YZT Package
8-Pin DSBGA
Bottom View

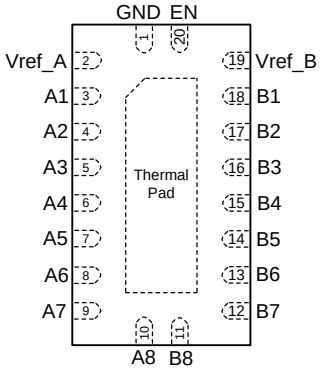


DQE Package
8-Pin X2SON
Transparent Top View



LSF0108

RKS Package
20-Pin VQFN
Transparent Top View



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. UNLESS OTHERWISE NOTED, this document contains ADVANCE INFORMATION for pre-production products; subject to change without notice.

Table of Contents

1 Features ... 1
2 Applications ... 1
3 Description ... 1
4 Revision History ... 2
5 Pin Configuration and Functions ... 4
6 Specifications ... 5
6.1 Absolute Maximum Ratings ... 5
6.2 ESD Ratings ... 5
6.3 Recommended Operating Conditions ... 5
6.4 Thermal Information: LSF0101, LSF0108 ... 6
6.5 Thermal Information: LSF0102 ... 6
6.6 Electrical Characteristics ... 6
6.7 LSF0101/02 AC Performance (Translating Down) Switching Characteristics , V_{GATE} = 3.3 V ... 7
6.8 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 3.3 V ... 7
6.9 LSF0101/02 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V ... 7
6.10 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V ... 7
6.11 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V ... 7
6.12 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V ... 7
6.13 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V ... 8
6.14 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V ... 8
6.15 Typical Characteristics ... 8
7 Parameter Measurement Information ... 9
8 Detailed Description ... 10
8.1 Overview ... 10
8.2 Functional Block Diagrams ... 10
8.3 Feature Description ... 11
8.4 Device Functional Modes ... 12
9 Application and Implementation ... 12
9.1 Application Information ... 12
9.2 Typical Applications ... 13
10 Power Supply Recommendations ... 16
11 Layout ... 16
11.1 Layout Guidelines ... 16
11.2 Layout Example ... 16
12 Device and Documentation Support ... 17
12.1 Related Links ... 17
12.2 Community Resources ... 17
12.3 Trademarks ... 17
12.4 Electrostatic Discharge Caution ... 17
12.5 Glossary ... 17
13 Mechanical, Packaging, and Orderable Information ... 17

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision G (February 2016) to Revision H — **Page**

- Added Advance Information note to Device Information table for DTQ package ... 1
- Added DTQ6 pinout drawing to *Pin Configurations and Functions* section (Advance Information). ... 4
- Added Advance Information note to LSF0101 Thermal Information table. ... 6
- General improvements to Application and Implementation section for clarity. ... 12

Changes from Revision F (October 2015) to Revision G — **Page**

- Added all available package dimensions in Device Information and changed the pin diagram description. ... 1

Changes from Revision E (July 2015) to Revision F — **Page**

- Changed Features from "Supports High Speed Translation, Greater Than 100 MHz" to "Supports Up to 100 MHz Up Translation and Greater Than 100 MHz Down Translation at ≤ 30pF Cap Load and Up To 40 MHz Up/Down Translation at 50 pF Cap Load." ... 1
- Updated all propagation delay tables changed from generic to specific LSF devices. ... 7

Changes from Revision D (October 2014) to Revision E — **Page**

- Deleted "Less Than 1.5 ns Max Propagation Delay" from Features. ... 1
- Updated ESD Ratings table. ... 5
- Increased MAX value for T_A, Operating free-air temperature, from 85°C to 125°C. ... 5

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Changes from Revision C (May 2014) to Revision D **Page**

- Changed bidirectional voltage level translation from 1.0 to 0.95 1
- Changed YZT package to fix view error. 1
- Changed YZT package to fix view error. 4
- Added pin numbers to *Pin Functions* table..... 4
- Added Vref_A footnote. 13

Changes from Revision B (May 2014) to Revision C **Page**

- Changed LSF0108 status from preview to production. 1
- Updated document title. 1
- Updated Handling Ratings table. 5

Changes from Revision A (January 2014) to Revision B **Page**

- Added LSF0108 to data sheet. 1

Changes from Original (December 2013) to Revision A **Page**

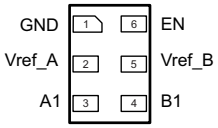
- Updated part number..... 1
- Updated *Electrical Characteristics* table..... 6

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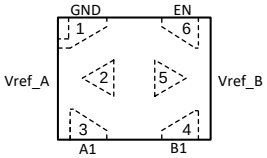
5 Pin Configuration and Functions

Pinout drawings are not to scale.

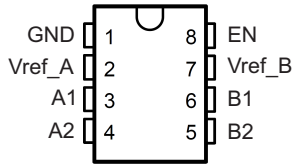
LSF0101 DRY Package
6-Pin SON
Transparent Top View



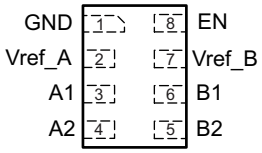
LSF0101 DTQ Package - Advance Information
6-Pin X2SON
Transparent Top View



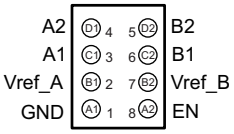
LSF0102 DCT or DCU Package
8-Pin SM8 or VSSOP
Top View



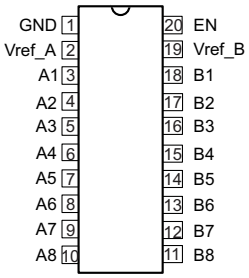
LSF0102 DQE Package
8-Pin X2SON
Transparent Top View



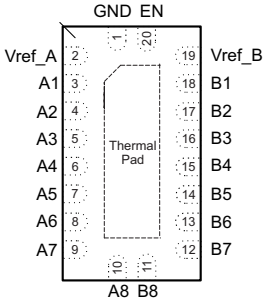
LSF0102 YZT Package
8-Pin DSBGA
Bottom View



LSF0108 PW Package
20-Pin TSSOP
Top View



LSF0108 RKS Package
20-Pin VQFN
Transparent Top View



Pin Functions

PIN				I/O	DESCRIPTION
NAME	DCT, DCU, DQE, YZT NO.	DRY, DTQ NO.	PW or RKS NO.		
An	3, 4	3	3 to 10	I/O	Auto-Bidirectional Data port
Bn	6, 5	4	18 to 11	I/O	
EN	8	6	20	I	Enable input; connect to Vref_B and pull-up through a high resistor (200 kΩ). See Using the Enable Pin with the LSF Family
GND	1	1	1	—	Ground
Vref_A	2	2	2	—	Reference supply voltage. For proper device biasing, see *Application and Implementation* and Understanding the Bias Circuit for the LSF Family.
Vref_B	7	5	19	—	

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6 Specifications

6.1 Absolute Maximum Ratings(1)

over operating free-air temperature (unless otherwise noted)

			MIN	MAX	UNIT
V_I	Input voltage(2)		–0.5	7	V
$V_{I/O}$	Input/output voltage(2)		–0.5	7	V
	Continuous channel current			128	mA
I_{IK}	Input clamp current	$V_I < 0$		–50	mA
T_J	Junction Temperature			150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and input/output negative-voltage ratings may be exceeded if the input and input/output clamp-current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
$V_{I/O}$	Input/output voltage	0	5	V
$V_{ref_A/B/EN}$	Reference voltage	0	5	V
I_{PASS}	Pass transistor current		64	mA
T_A	Operating free-air temperature	–40	125	°C

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6.4 Thermal Information: LSF0101, LSF0108

THERMAL METRIC[1]		LSF0101		LSF0108		UNIT
		DTQ (X2SON)[2]	DRY (SON)	RKS (VQFN)	PW (TSSOP)	
		6 PINS	6 PINS	20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	294.4	407.0	49.3	106.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	188.9	285.2	45.9	41.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	216.8	271.6	20.6	57.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	26.5	113.5	2.5	4.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	216.0	271.0	20.6	47.0	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	3.4	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
(2) Advance Information

6.5 Thermal Information: LSF0102

THERMAL METRIC[1]		LSF0102				UNIT
		DCU (US8)	DCT (SM8)	DQE (X2SON)	YZT (DSBGA)	
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.1	189.6	246.5	125.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	89.1	119.6	149.1	1.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	88.8	102.1	100.0	62.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	8.3	44.5	17.1	3.4	°C/W
ψ_{JB}	Junction-to-board characterization parameter	88.4	101.0	99.8	62.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

6.6 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP[1]	MAX	UNIT
V_{IK}	I_I = –18 mA,	V_{EN} = 0				–1.2	V
I_{IH}	V_I = 5 V	V_{EN} = 0				5.0	µA
I_{CC}	V_{ref_B} = V_{EN} = 5.5 V, V_{ref_A} = 4.5 V or 1 V, I_O = 0, V_I = V_{CC} or GND				1		µA
$C_{I(ref_A/B/EN)}$	V_I = 3 V or 0				11		pF
$C_{io(off)}$	V_O = 3 V or 0,	V_{EN} = 0			4.0	6.0	pF
$C_{io(on)}$	V_O = 3 V or 0,	V_{EN} = 3 V			10.5	12.5	pF
r_{on}[2]	V_I = 0,	I_O = 64 mA	V_{ref_A} = 3.3 V; V_{ref_B} = V_{EN} = 5 V		8.0		Ω
			V_{ref_A} = 1.8 V; V_{ref_B} = V_{EN} = 5 V		9.0		
			V_{ref_A} = 1.0 V; V_{ref_B} = V_{EN} = 5 V		10		
	V_I = 0,	I_O = 32 mA	V_{ref_A} = 1.8 V; V_{ref_B} = V_{EN} = 5 V		10		Ω
			V_{ref_A} = 2.5 V; V_{ref_B} = V_{EN} = 5 V		15		
	V_I = 1.8 V,	I_O = 15 mA	V_{ref_A} = 3.3 V; V_{ref_B} = V_{EN} = 5 V		9.0		Ω
	V_I = 1.0 V,	I_O = 10 mA	V_{ref_A} = 1.8 V; V_{ref_B} = V_{EN} = 3.3 V		18		Ω
	V_I = 0 V,	I_O = 10 mA	V_{ref_A} = 1.0 V; V_{ref_B} = V_{EN} = 3.3 V		20		Ω
	V_I = 0 V,	I_O = 10 mA	V_{ref_A} = 1.0 V; V_{ref_B} = V_{EN} = 1.8 V		30		Ω

(1) All typical values are at T_A = 25°C.
(2) Measured by the voltage drop between the A and B pins at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) pins.

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6.7 LSF0101/02 AC Performance (Translating Down) Switching Characteristics , V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 3.3 V, V_{IL} = 0, and V_M = 1.15 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.1		0.7		0.3		ns
t_{PHL}			1.2		0.8		0.4		

6.8 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 3.3 V, V_{IL} = 0, and V_M = 1.15 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.9		1.4		0.75		ns
t_{PHL}			2		1.5		0.85		

6.9 LSF0101/02 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 2.5 V, V_{IL} = 0, and V_M = 0.75 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.2		0.8		0.35		ns
t_{PHL}			1.3		1		0.5		

6.10 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 2.5 V, V_{IL} = 0, and V_M = 0.75 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	2		1.45		0.8		ns
t_{PHL}			2.1		1.55		0.9		

6.11 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 2.3 V, V_{IL} = 0, V_T = 3.3 V, V_M = 1.15 V and R_L = 300 (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1		0.8		0.4		ns
t_{PHL}			1		0.9		0.4		

6.12 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 2.3 V, V_{IL} = 0, V_T = 3.3 V, V_M = 1.15 V and R_L = 300 (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	2.1		1.55		0.9		ns
t_{PHL}			2.2		1.65		1		

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6.13 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 1.5 V, V_{IL} = 0, V_T = 2.5 V, V_M = 0.75 V and R_L = 300 (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.1		0.9		0.45		ns
t_{PHL}			1.3		1.1		0.6		

6.14 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 1.5 V, V_{IL} = 0, V_T = 2.5 V, V_M = 0.75 V and R_L = 300 (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.8		1.35		0.8		ns
t_{PHL}			1.9		1.45		0.9		

6.15 Typical Characteristics

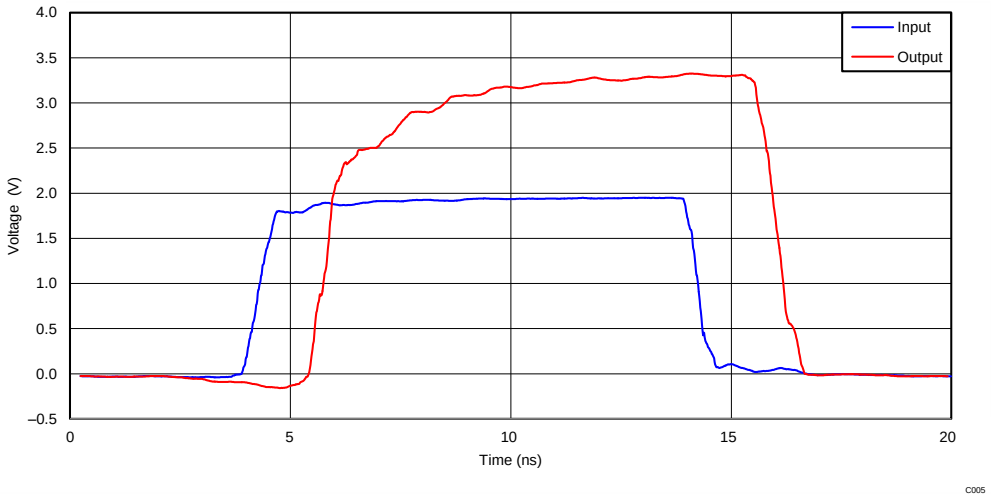
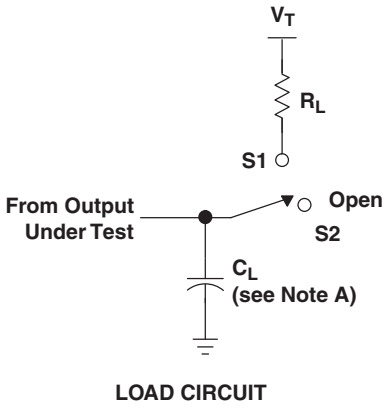


Figure 1. Signal Integrity (1.8 to 3.3 V Up Translation at 50 MHz)

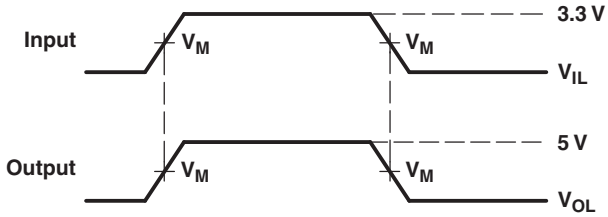
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7 Parameter Measurement Information

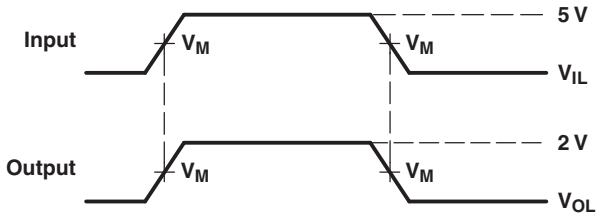


LOAD CIRCUIT

USAGE	SWITCH
Translating up	S1
Translating down	S2



TRANSLATING UP



TRANSLATING DOWN

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
C. The outputs are measured one at a time, with one transition per measurement.

Figure 2. Load Circuit for Outputs

8 Detailed Description

8.1 Overview

The LSF family can be used in level-translation applications for interfacing devices or systems operating with one another, that operate at different interface voltages. The LSF family is ideal for use in applications where an open-drain driver is connected to the data I/Os. With appropriate pull-up resistors and layout, LSF can achieve 100 MHz. The LSF family can also be used in applications where a push-pull driver is connected to the data I/Os. For an overview of device setup and operation, see *The Logic Minute* training series on *Understanding the LSF Family of Bidirectional, Multi-Voltage Level Translators*.

8.2 Functional Block Diagrams

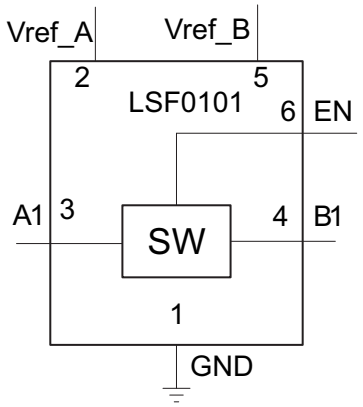


Figure 3. LSF0101 Functional Block Diagram

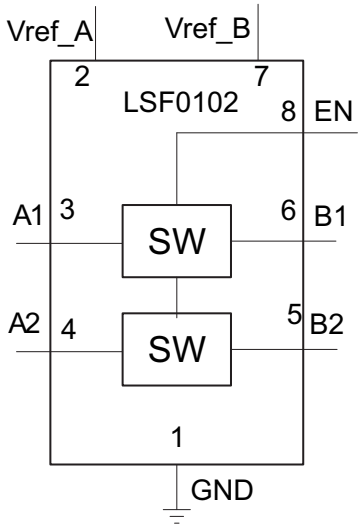


Figure 4. LSF0102 Functional Block Diagram

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Functional Block Diagrams (continued)

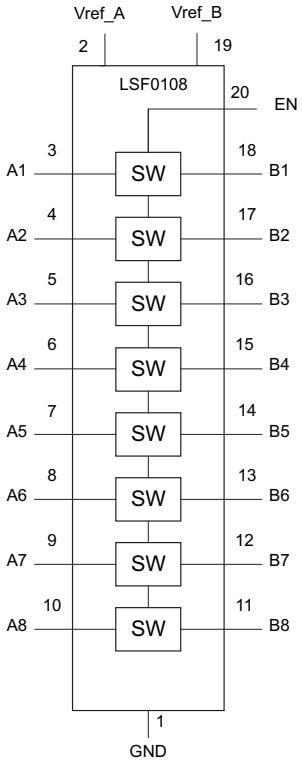


Figure 5. LSF0108 Functional Block Diagram

8.3 Feature Description

8.3.1 Auto Bidirectional Voltage Translation

All devices in the LSF family are auto bidirectional voltage level translators that are operational from 0.95 to 4.5 V on the Vref_A supply and from 1.8 to 5.5 V on the Vref_B supply. This allows bidirectional voltage translation between 0.95 V and 5.5 V without the need for a direction pin in open-drain or push-pull applications. LSF family supports level translation applications with transmission speeds greater than 100 Mbps for open-drain systems using a 30-pF capacitance and 250-Ω pullup resistor. For additional details on the recommended setup and operation of the LSF family of devices, see the *Understanding the LSF Family of Bidirectional, Multi-Voltage Level Translators* training series.

8.3.2 Output Enable

To enable the I/O pins, the EN input should be tied directly to Vref_B during operation. To ensure the high impedance state during power-up, power-down, or during operation, the EN pin must be LOW. The EN pin should always be tied directly to the Vref_B pin and is recommended to be disabled by an open-drain driver without a pullup resistor. For additional details on how to use the enable pin, see the *Using the Enable Pin with the LSF Family* video.

Table 1. Enable Pin Function Table

INPUT EN(1) PIN	Data Port State
Tied directly to Vref_B	An = Bn
L	Hi-Z

(1) EN is controlled by V_{ref_B} logic levels.

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8.4 Device Functional Modes

For each channel (n), when either the An or Bn port is LOW, the switch provides a low impedance path between the An and Bn ports; the corresponding Bn or An port will be pulled LOW. The low R_{ON} of the switch allows connections to be made with minimal propagation delay and signal distortion.

When the signal is being driven from Bn to An and the Bn port is driven HIGH, the switch will be OFF, clamping the voltage on the An port to the voltage set by Vref_A. When the signal is being driven from A to B and the An port is HIGH, the switch will be OFF and the Bn port will then driven to a voltage higher than Vref_A by the pullup resistor that is connected to the pull-up supply voltage ($V_{pu\#}$). This functionality allows seamless translation between higher and lower voltages selected by the user, without the need for directional control.

Refer to Table 1 for a summary of device operation. For additional details on the functional operation of the LSF family of devices, see the *Down Translation with the LSF Family* and *Up Translation with the LSF Family* videos.

Table 2. Device Functionality

Signal Direction (1)	Input State	Switch State	Functionality
B to A (Down Translation)	B = LOW	ON (Low Impedance)	A-side voltage is pulled low through the switch to the B-side voltage
	B = HIGH	OFF (High Impedance)	A-side voltage is clamped at Vref_A (2)
A to B (Up Translation)	A = LOW	ON (Low Impedance)	B-side voltage is pulled low through the switch to the A-side voltage
	A = HIGH	OFF (High Impedance)	B-side voltage is clamped at Vref_A and then pulled up to the Vpu# supply voltage

(1) The downstream channel should not be actively driven through a low impedance driver, or else there may be bus contention.
(2) The A-side can have a pullup to Vref_A for additional current drive capability or may also be pulled above Vref_A with a pullup resistor. Specifications in the Recommended Operating Conditions should always be followed.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LSF devices are able to perform voltage translation for open-drain or push-pull interfaces. Table 3 provides common interfaces and the corresponding device recommendation from the LSF family which supports the corresponding bit count.

Table 3. Voltage Translator for Common Interfaces

Part Name	Channel Number	Interface
LSF0101	1	GPIO
LSF0102	2	GPIO, MDIO, SMBus, PMBus, I^2C
LSF0108	8	GPIO, MDIO, SDIO, SVID, UART, SMBus, PMBus, I^2C, SPI

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9.2 Typical Applications

9.2.1 Open-Drain Interface (I^2C, PMBus, SMBus, GPIO)

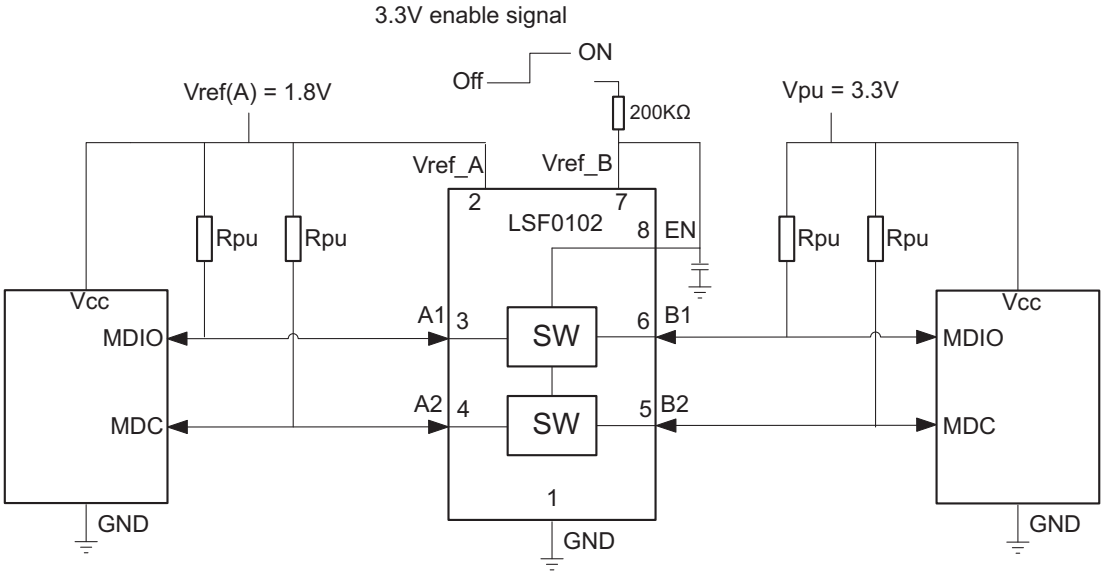


Figure 6. Typical Application Circuit for Open-Drain Translation (MDIO shown as an example)

9.2.1.1 Design Requirements

9.2.1.1.1 Enable, Disable, and Reference Voltage Guidelines

The LSF family has an EN input that is used to disable the device by setting EN LOW, placing all I/Os in the high-impedance state. Since the LSF family of devices are switch-type voltage translators, the power consumption is very low. TI recommends always enabling the LSF family for bidirectional applications (I^2C, SMBus, PMBus, or MDIO).

Table 4. Application Operating Condition

PARAMETER		MIN	TYP	MAX	UNIT
Vref_A (1)	reference voltage (A)	0.95		4.5	V
Vref_B	reference voltage (B)	Vref_A + 0.8		5.5	V
$V_{I(EN)}$	input voltage on EN pin	Vref_A + 0.8		5.5	V
Vpu	pull-up supply voltage	0		Vref_B	V

(1) Vref_A is required to be the lowest voltage level across all inputs and outputs.

The 200 kΩ, pull-up resistor is required to allow Vref_B to regulate the EN input and properly bias the device for translation. For additional details on device biasing, see the *Understanding the Bias Circuit for the LSF Family* video. A filter capacitor on Vref_B is recommended. Also Vref_B and $V_{I(EN)}$ are recommended to be 1.0 V higher than Vref_A for best signal integrity.

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Bidirectional Translation

For the bidirectional translation configuration (higher voltage to lower voltage or lower voltage to higher voltage), the EN input must be connected to Vref_B and both pins must be pulled up to the HIGH side Vpu through a pull-up resistor (typically 200 kΩ). This allows Vref_B to regulate the EN input and bias the channels for proper translation. A filter capacitor on Vref_B is recommended for a stable supply at the device. The master output driver can be push-pull or open-drain (pull-up resistors may be required) and the slave device output can be push-pull or open-drain (pull-up resistors are required to pull the Bn outputs to Vpu).

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If either output is push-pull, data must be unidirectional or the outputs must be tri-state and be controlled by some direction-control mechanism to prevent HIGH-to-LOW bus contention in either direction. If both outputs are open-drain, no direction control is needed.

When Vref_B is connected through a 200-kΩ resistor to a 3.3-V Vpu power supply and Vref_A is set 1.8 V, as shown in Figure 6, the A1 and A2 channels have a maximum output voltage equal to Vref_A, and the B1 and B2 channels have has a maximum output voltage equal to Vpu.

9.2.1.2.2 Pull-up Resistor Sizing

The pull-up resistor value needs to limit the current through the pass transistor when it is in the ON state to about 15 mA. This ensures a voltage drop of 260 mV to 350 mV to have a valid LOW signal on the downstream channel. If the current through the pass transistor is higher than 15 mA, the voltage drop is also higher in the ON state. To set the current through each pass transistor at 15 mA, calculate the pull-up resistor value using the following equation:

$$Rpu = (Vpu – 0.35\ V) / 0.015\ A \quad (1)$$

Table 5 summarizes resistor values, reference voltages, and currents at 15 mA, 10 mA, and 3 mA. The resistor value shown in the +10% column (or a larger value) should be used to ensure that the voltage drop across the transistor is 350 mV or less. The external driver must be able to sink the total current from the resistors on both sides of the LSF family device at 0.175 V, although the 15 mA applies only to current flowing through the LSF family device.

Table 5. Pull-up Resistor Values(1)(2)

V_{DPU}	15 mA		10 mA		3 mA	
	NOMINAL (Ω)	+10%(3) (Ω)	NOMINAL (Ω)	+10%(3) (Ω)	NOMINAL (Ω)	+10%(3) (Ω)
5 V	310	341	465	512	1550	1705
3.3 V	197	217	295	325	983	1082
2.5 V	143	158	215	237	717	788
1.8 V	97	106	145	160	483	532
1.5 V	77	85	115	127	383	422
1.2 V	57	63	85	94	283	312

(1) Calculated for V_{OL} = 0.35 V
(2) Assumes output driver V_{OL} = 0.175 V at stated current
(3) +10% to compensate for V_{DD} range and resistor tolerance

9.2.1.3 Application Curve

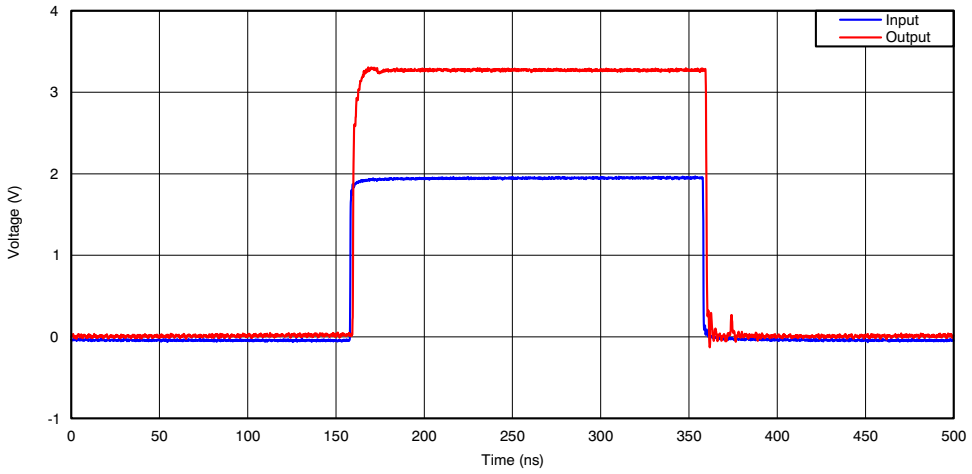


Figure 7. Open Drain Translation (1.8 V to 3.3 V at 2.5 MHz)

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9.2.2 Mixed-Mode Voltage Translation

The supply voltage ($V_{pu\#}$) for each channel can be individually set with a pull-up resistor. An example of this mixed-mode multi-voltage translation is shown in Figure 8. For additional details on multi-voltage translation, see the *Multi-voltage Translation with the LSF Family* video.

With the Vref_B pulled up to 5V and Vref_A connected to 1.8V, all channels will be clamped to 1.8V at which point a pullup can be used to define the high level voltage for a given channel.

- **Push-Pull Down Translation (5V to 1.8V):** Channel 1 is an example of this setup. When B1 is 5V, A1 is clamped to 1.8V, and when B1 is LOW, A1 is driven LOW through the switch.
- **Push-Pull Up Translation (1.8V to 5V)**: Channel 2 is an example of this setup. When A2 is 1.8V, the switch is high impedance and the B2 channel is pulled up to 5V. When A2 is LOW, B2 is driven LOW through the switch.
- **Push-Pull Down Translation (3.3V to 1.8V):** Channels 3 and 4 are examples of this setup. When either B3 or B4 are driven to 3.3V, A3 or A4 are clamped to 1.8V, and when either B3 or B4 are LOW, A3 or A4 are driven LOW through the switch.
- **Open-Drain Bidirectional Translation (3.3V ↔ 1.8V):** Channels 5 through 8 are examples of this setup. These channels are for bidirectional operation for I^2C and MDIO to translate between 1.8V and 3.3V with open-drain drivers.

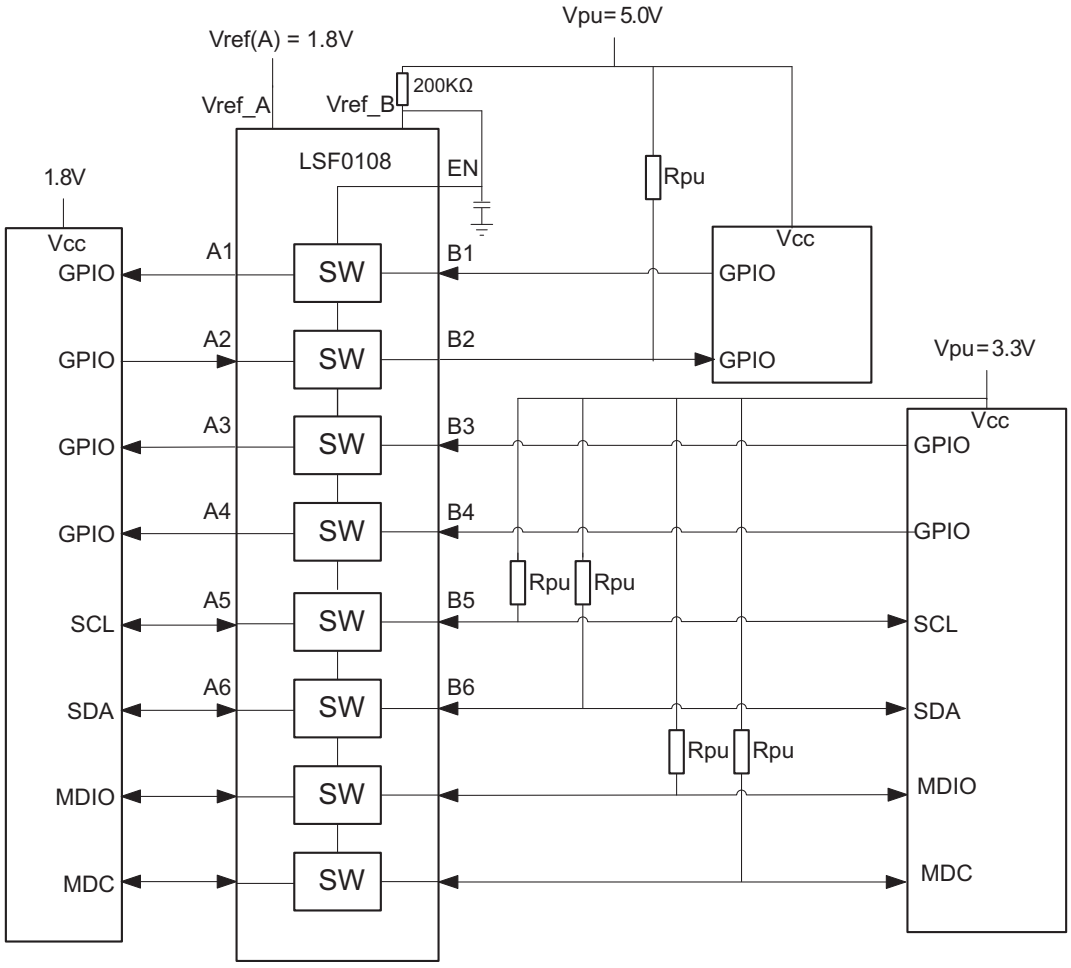


Figure 8. Multi-Voltage Translation with the LSF0108

10 Power Supply Recommendations

There are no power sequence requirements for the LSF family. For recommended operating voltages for all supply and input pins, see Table 6.

Table 6. Recommended Operating Voltages

PARAMETER		MIN	TYP	MAX	UNIT
Vref_A (1)	reference voltage (A)	0.95		4.5	V
Vref_B	reference voltage (B)	Vref_A + 0.8		5.5	V
$V_{I(EN)}$	input voltage on EN pin	Vref_A + 0.8		5.5	V
Vpu	pull-up supply voltage	0		Vref_B	V

(1) Vref_A is required to be the lowest voltage level across all inputs and outputs.

11 Layout

11.1 Layout Guidelines

Because the LSF family is a switch-type level translator, the signal integrity is highly related with a pull-up resistor and PCB capacitance condition.

- Short signal trace as possible to reduce capacitance and minimize stub from pull-up resistor.
- Place LSF close to high voltage side.
- Select the appropriate pull-up resistor that applies to translation levels and driving capability of transmitter.

11.2 Layout Example

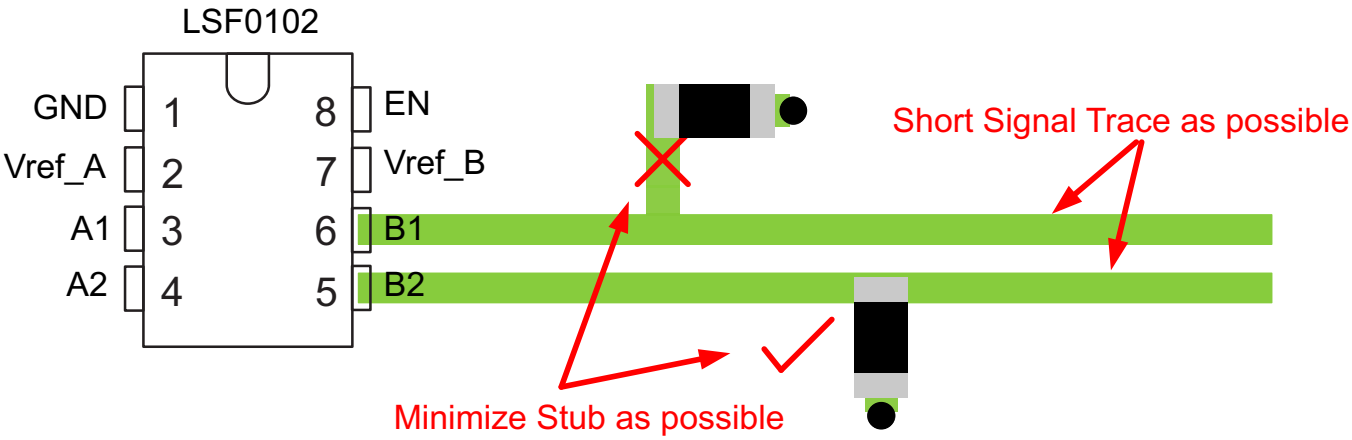


Figure 9. Short Trace Layout

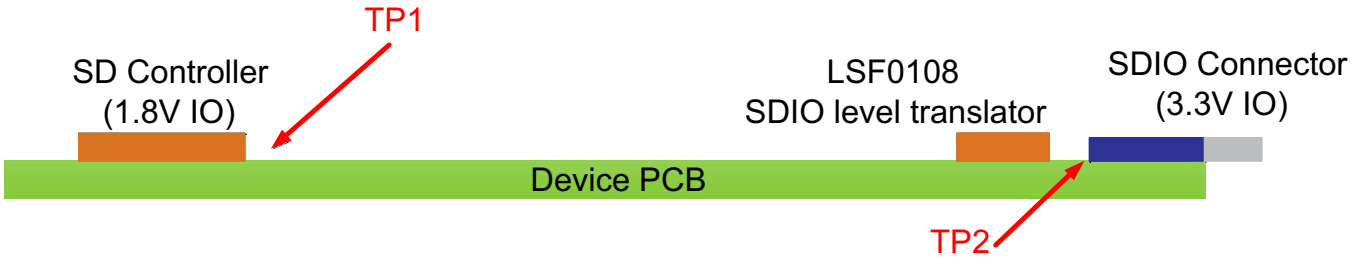


Figure 10. Device Placement

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12 Device and Documentation Support

12.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 7. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
LSF0101	Click here	Click here	Click here	Click here	Click here
LSF0102	Click here	Click here	Click here	Click here	Click here
LSF0108	Click here	Click here	Click here	Click here	Click here

1. LSF Translator Family Evaluation Module
2. The Logic Minute Video Training Series on Understanding the LSF Family of Devices
   - *Introduction - Voltage Level Translation with the LSF Family*
   - *Understanding the Bias Circuit for the LSF Family*
   - *Using the Enable Pin with the LSF Family*
   - *Translation Basics with the LSF Family*
   - *Down Translation with the LSF Family*
   - *Up Translation with the LSF Family*
   - *Multi-Voltage Translation with the LSF Family*
   - *Single Supply Translation with the LSF Family*
3. *Voltage Level Translation with the LSF Family* Application Note
4. *Biasing Requirements for TXS, TXB, and LSF Auto-Bidirectional Translators* Application Note

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LSF0101DRYR	ACTIVE	SON	DRY	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD	Samples
LSF0101DTQR	PREVIEW	X2SON	DTQ	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	FC	
LSF0102DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	NG2 (S, Y)	Samples
LSF0102DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-40 to 125	(G2, NG2P, NG2S) NY	Samples
LSF0102DQER	ACTIVE	X2SON	DQE	8	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0102YZTR	ACTIVE	DSBGA	YZT	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0108PWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples
LSF0108RKSR	ACTIVE	VQFN	RKS	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples
PLSF0101DTQR	ACTIVE	X2SON	DTQ	6	3000	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF LSF0102, LSF0108 :

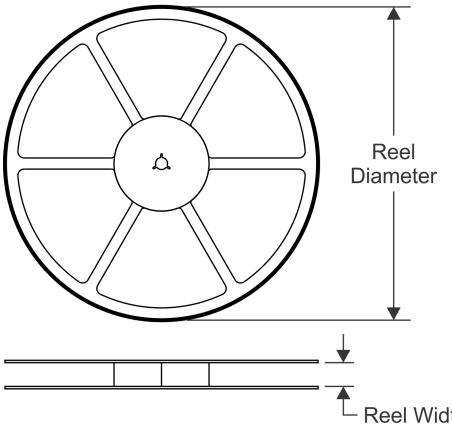
- Automotive: LSF0102-Q1, LSF0108-Q1

NOTE: Qualified Version Definitions:

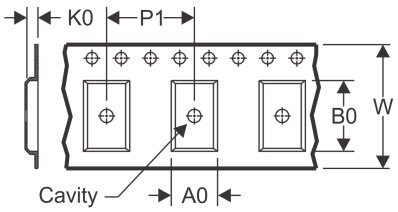
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

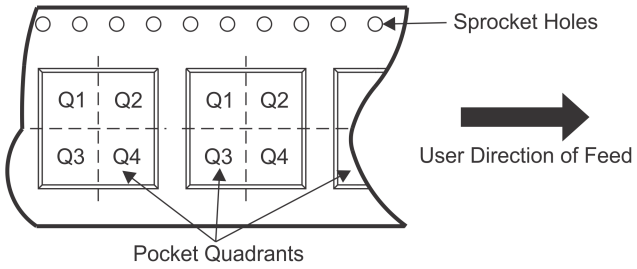


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

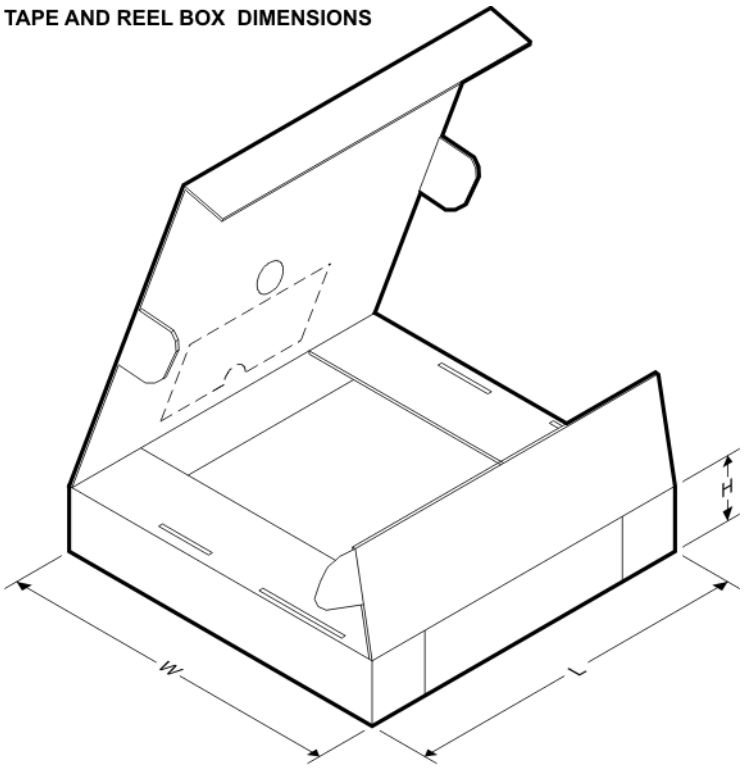
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LSF0101DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
LSF0102DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.05	3.3	1.0	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DQER	X2SON	DQE	8	5000	180.0	9.5	1.15	1.6	0.5	4.0	8.0	Q1
LSF0102YZTR	DSBGA	YZT	8	3000	180.0	8.4	1.02	2.02	0.75	4.0	8.0	Q1
LSF0108PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
LSF0108RKSR	VQFN	RKS	20	3000	177.8	12.4	2.73	4.85	1.03	4.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

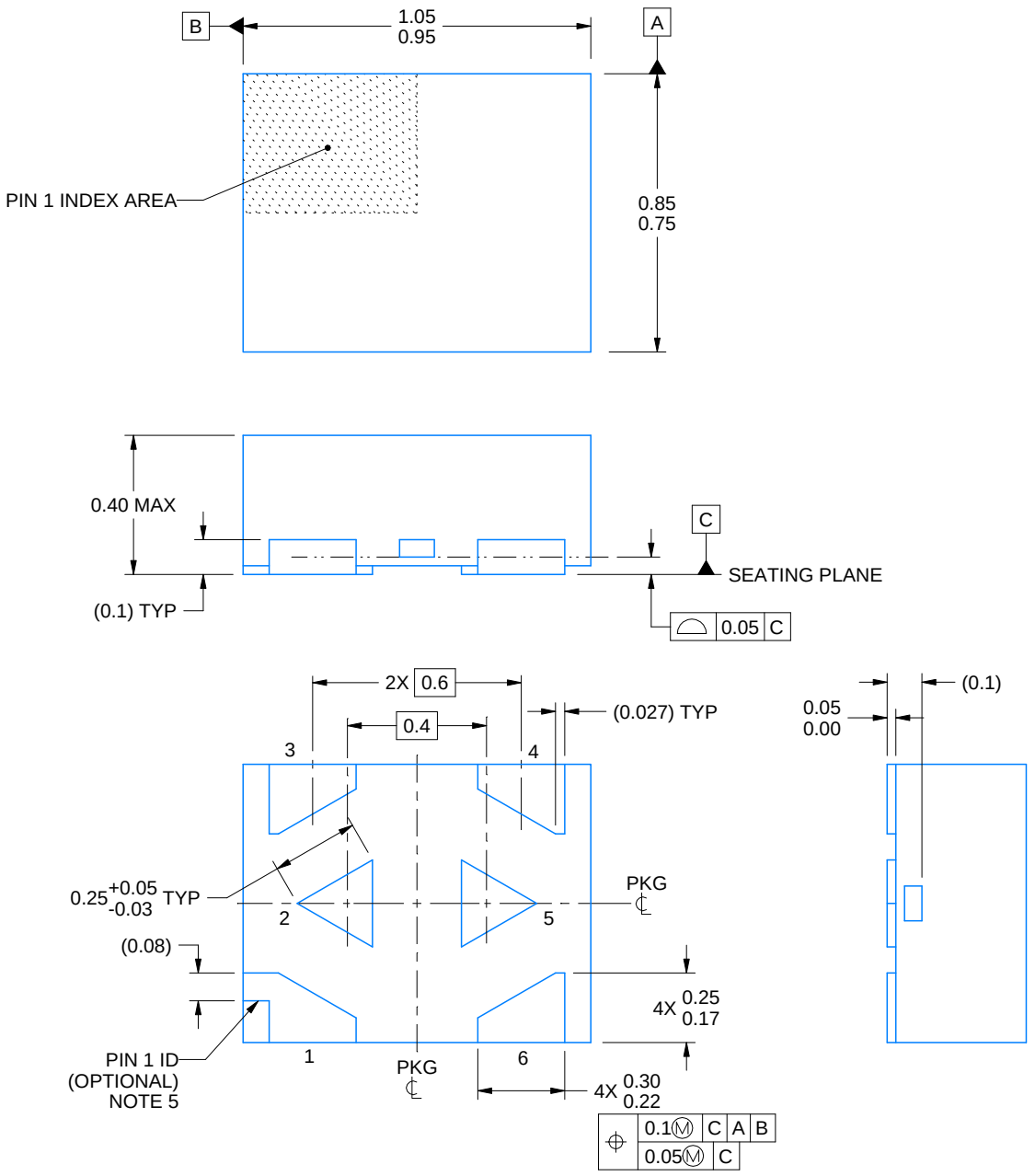
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LSF0101DRYR	SON	DRY	6	5000	184.0	184.0	19.0
LSF0102DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
LSF0102DQER	X2SON	DQE	8	5000	184.0	184.0	19.0
LSF0102YZTR	DSBGA	YZT	8	3000	182.0	182.0	20.0
LSF0108PWR	TSSOP	PW	20	2000	364.0	364.0	27.0
LSF0108RKSR	VQFN	RKS	20	3000	202.0	201.0	28.0

DTQ0006A

PACKAGE OUTLINE

X2SON - 0.4 mm max height

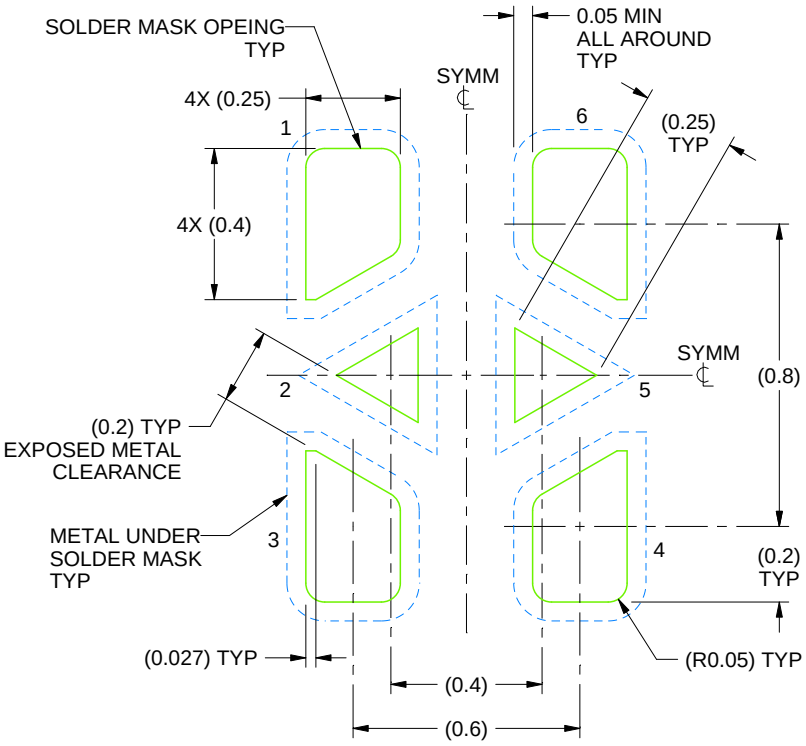
PLASTIC SMALL OUTLINE - NO LEAD



4224056/A 11/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pads must be soldered to the printed circuit board for optimal thermal and mechanical performance.
4. The size and shape of this feature may vary.
5. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.

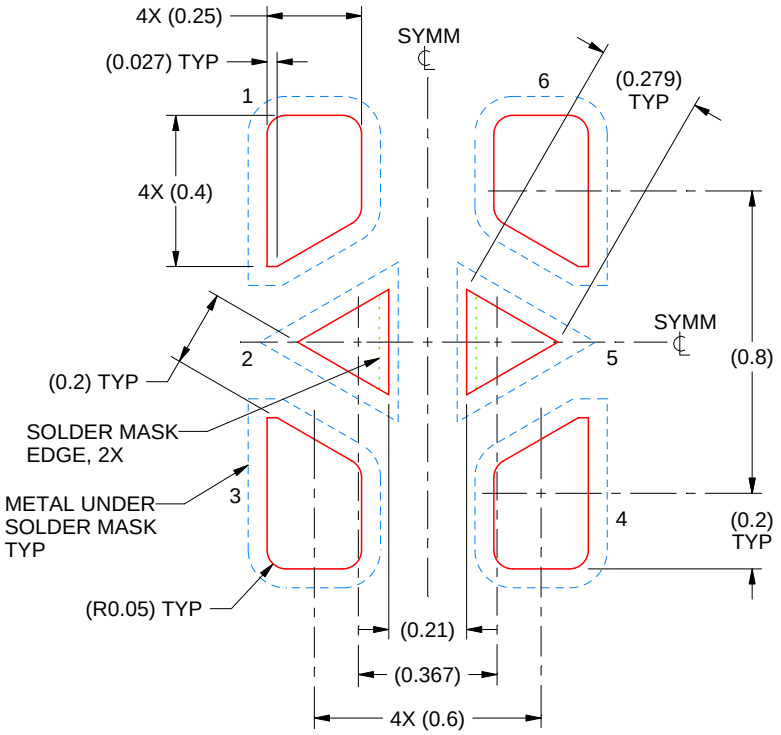


LAND PATTERN EXAMPLE
SOLDER MASK DEFINED
SCALE:50X

4224056/A 11/2017

NOTES: (continued)

6. This package is designed to be soldered to a thermal pads on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
7. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



SOLDER PASTE EXAMPLE
BASED ON 0.07 mm THICK STENCIL

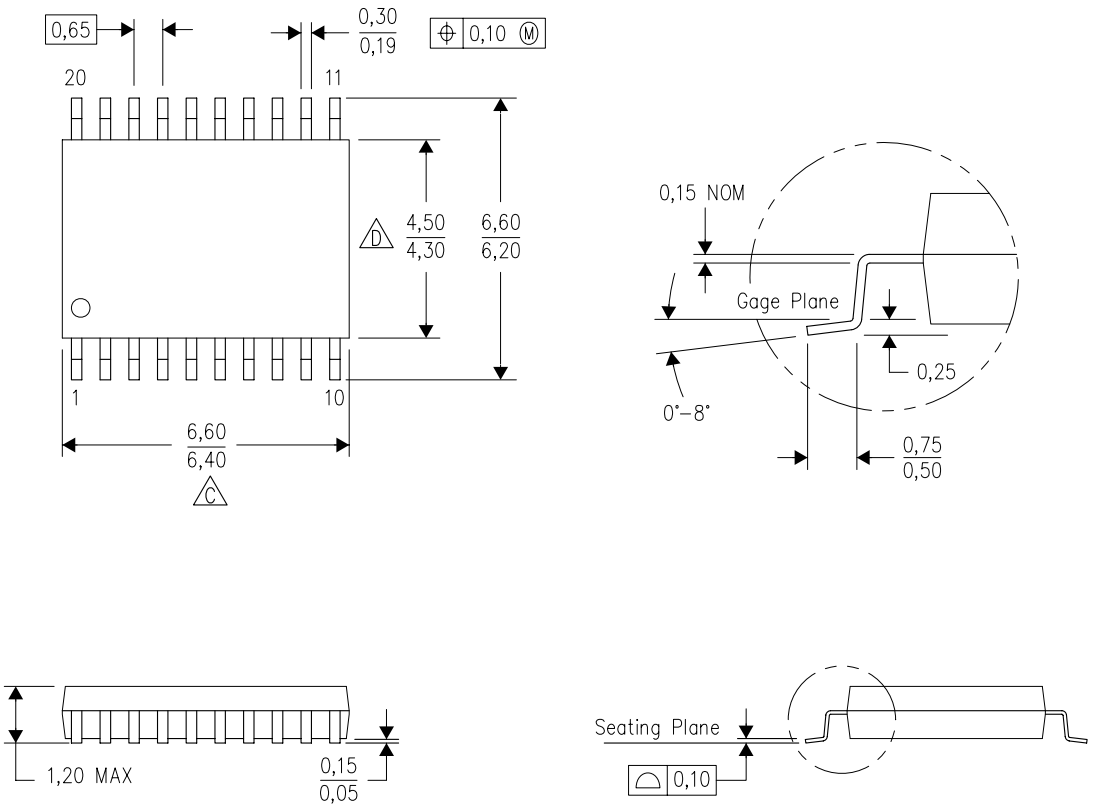
PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:50X

4224056/A 11/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

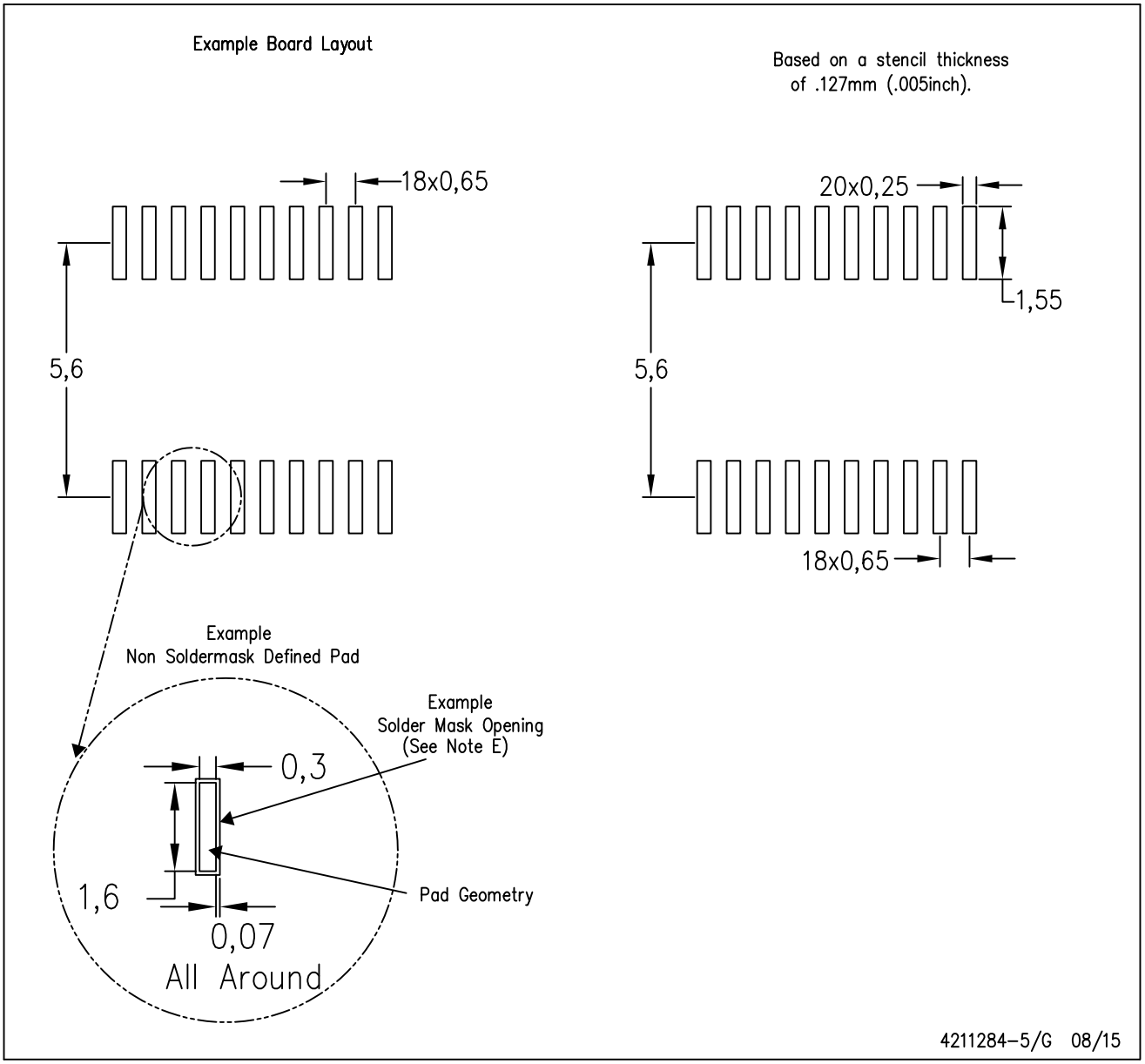
PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



4040064–5/G 02/11

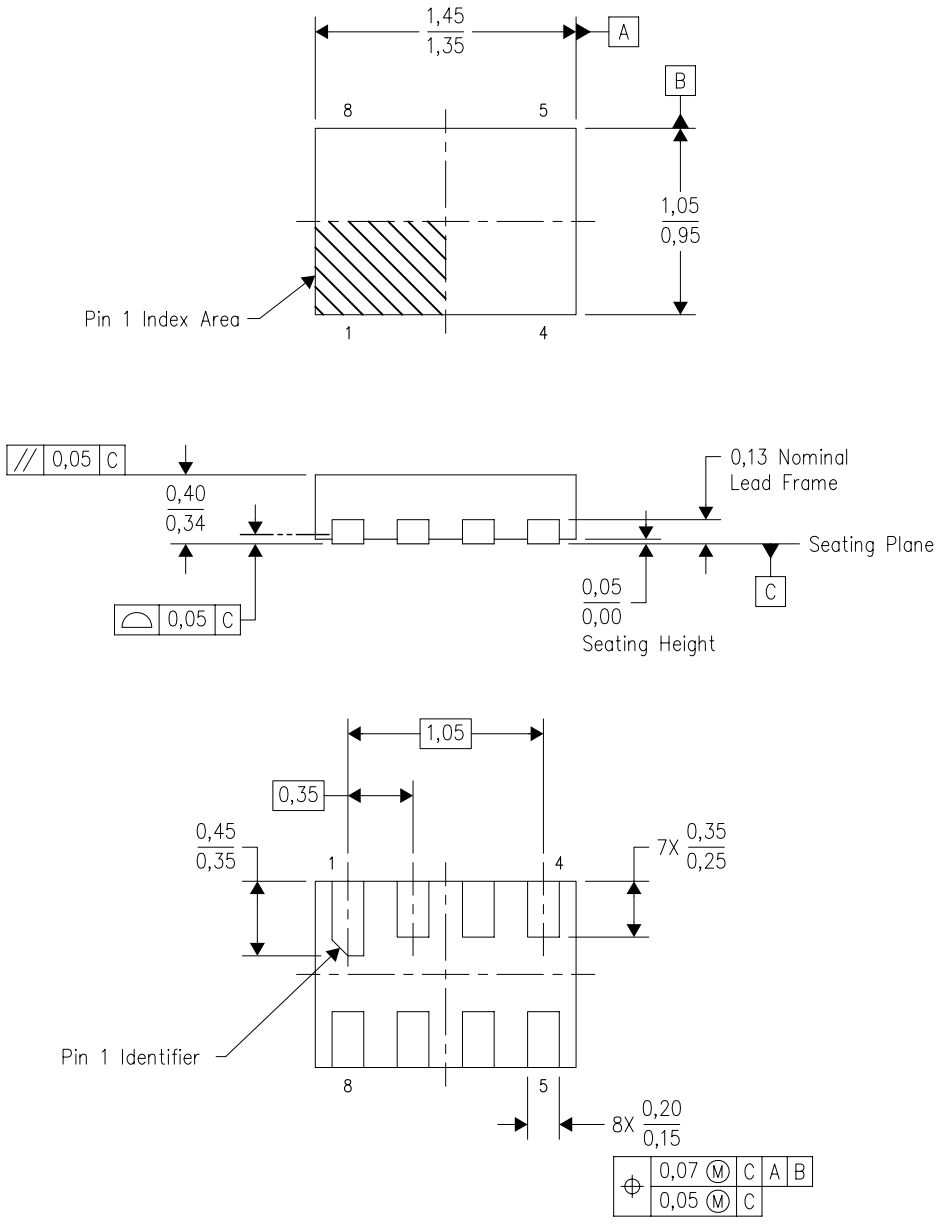
NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

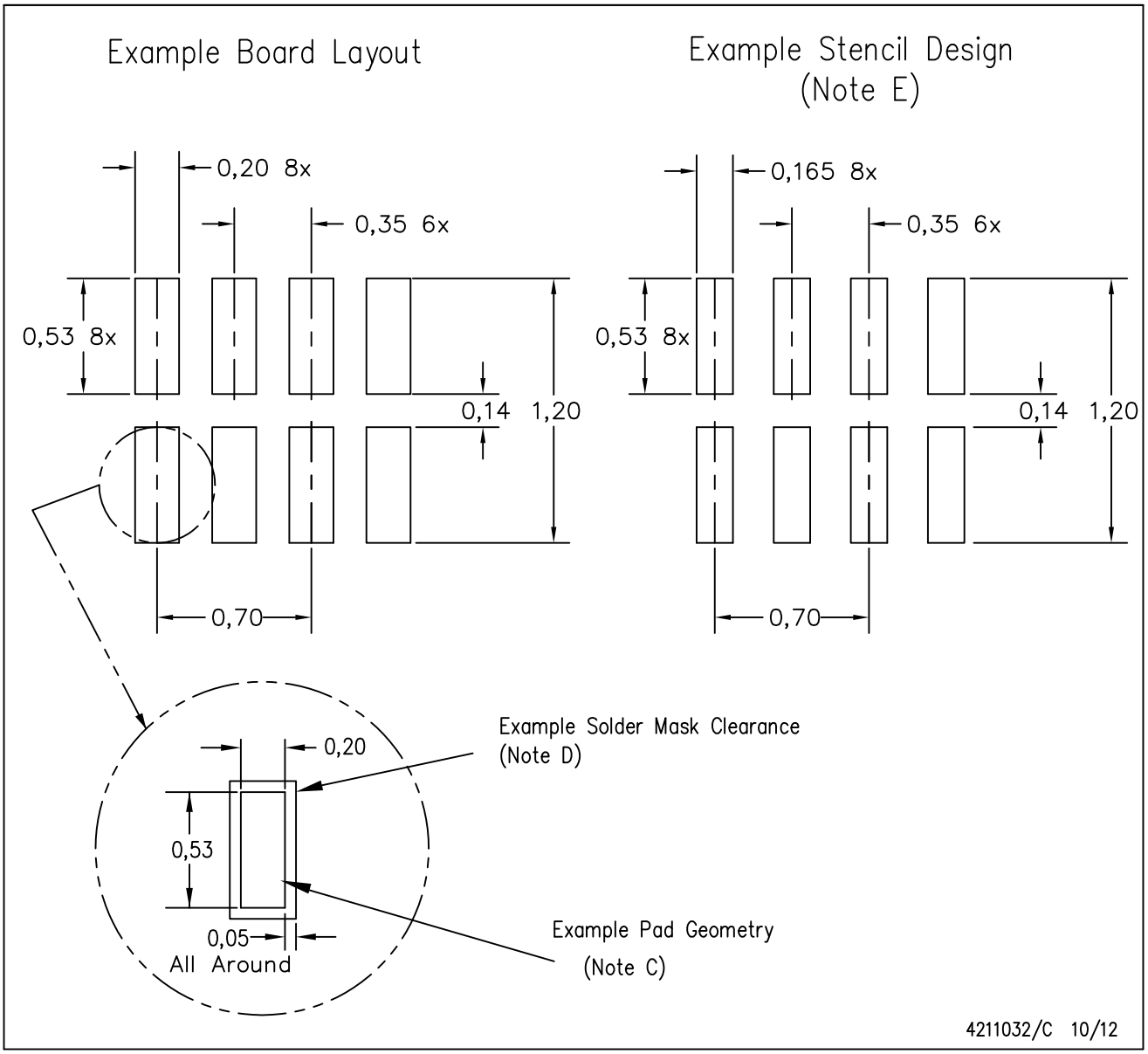
DQE (R–PX2SON–N8) PLASTIC SMALL OUTLINE NO–LEAD



4209779/B 10/2008

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. SON (Small Outline No–Lead) package configuration.
D. This package complies to JEDEC MO–287 variation X2EAF.

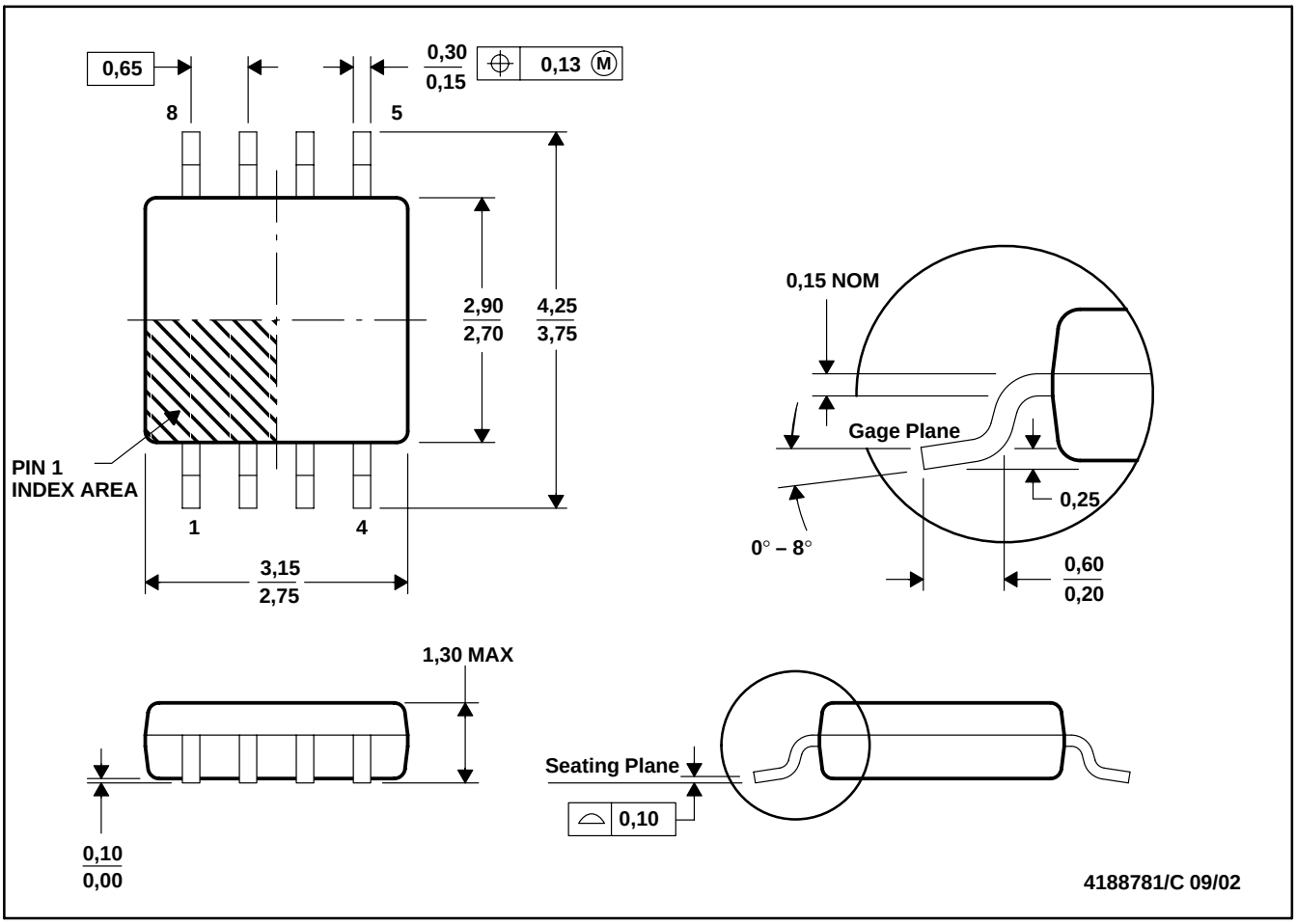
DQE (R–PX2SON–N8) PLASTIC SMALL OUTLINE NO–LEAD



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads. If 2 mil solder mask is outside PCB vendor capability, it is advised to omit solder mask.
E. Maximum stencil thickness 0,1016 mm (4 mils). All linear dimensions are in millimeters.
F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
G. Over–printing land for acceptable area ratio is not viable due to land width and bridging potential. Customer may further reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.
H. Suggest stencils cut with lasers such as Fiber Laser that produce the greatest positional accuracy.
I. Component placement force should be minimized to prevent excessive paste block deformation.

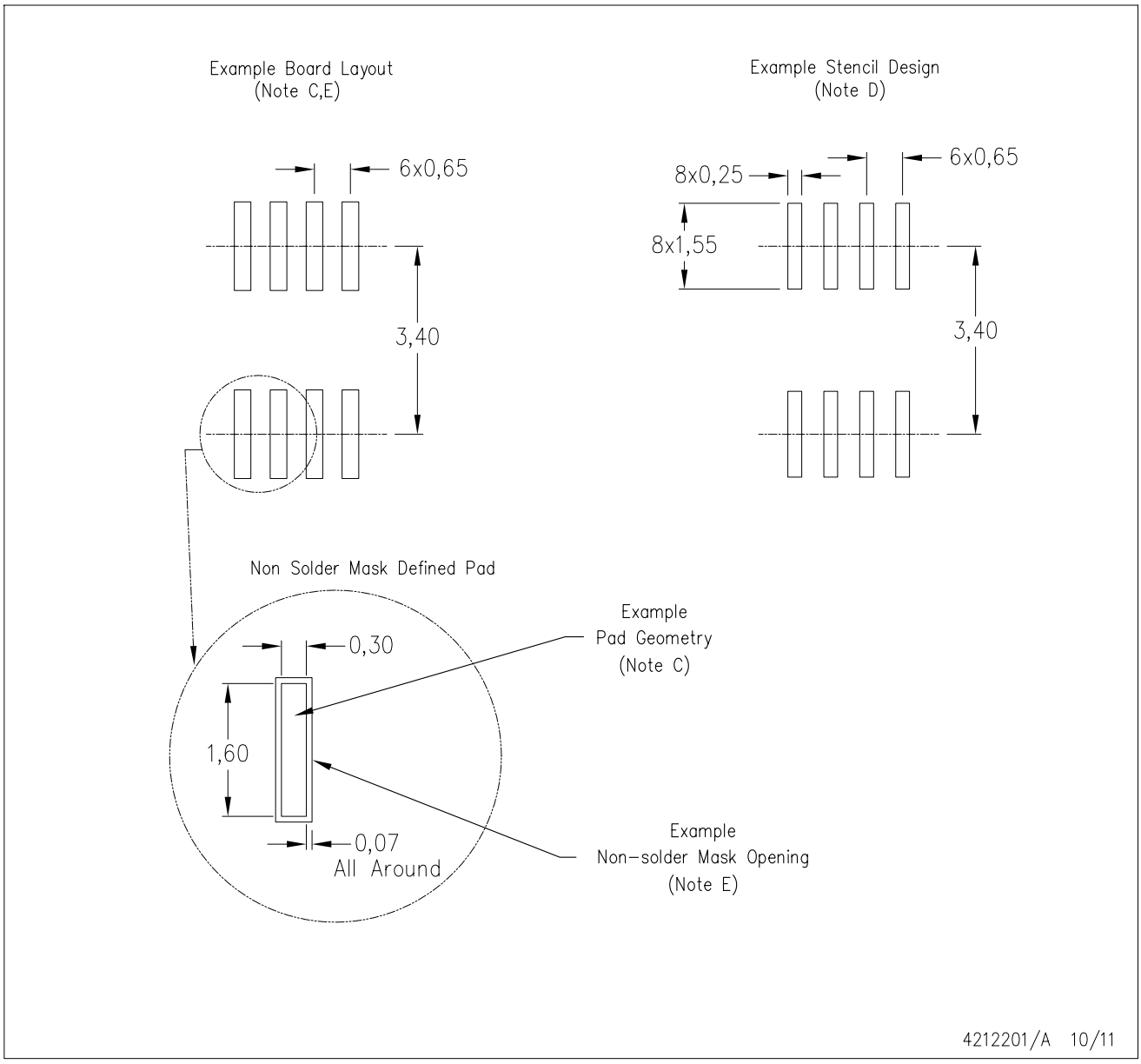
MPDS049B – MAY 1999 – REVISED OCTOBER 2002

DCT (R-PDSO-G8) **PLASTIC SMALL-OUTLINE PACKAGE**



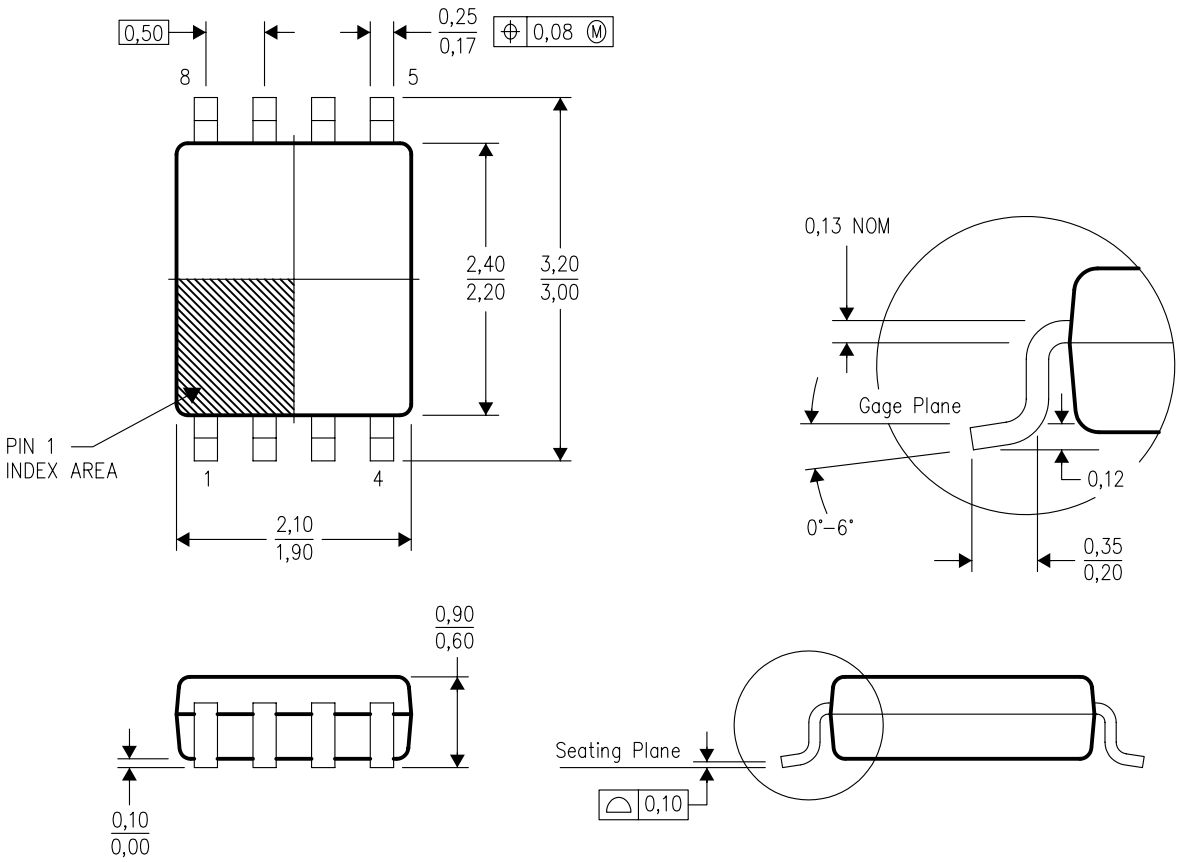
NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion
D. Falls within JEDEC MO-187 variation DA.

DCT (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

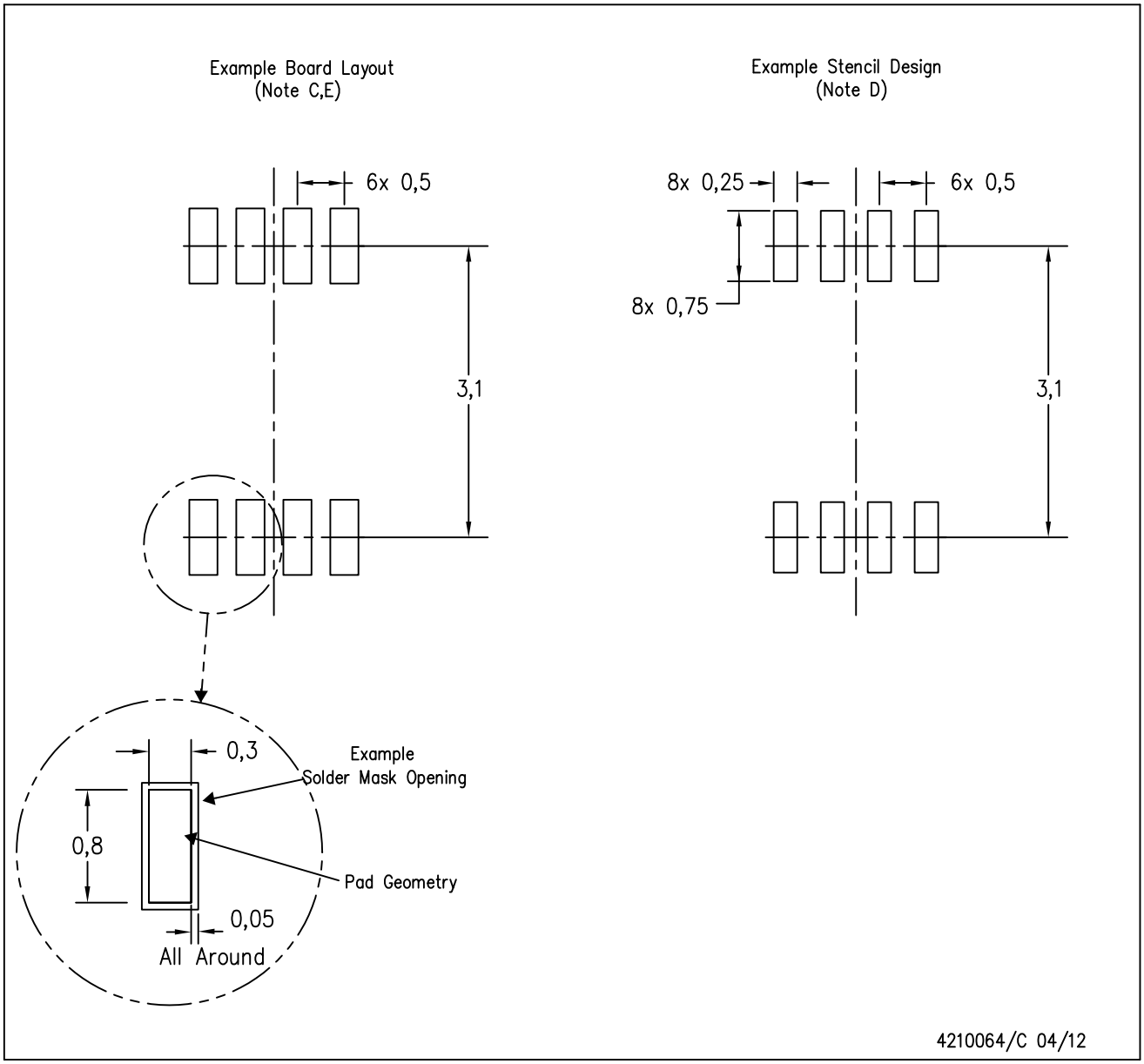
DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



4200503/F 07/05

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

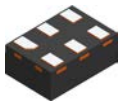
DRY 6 USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

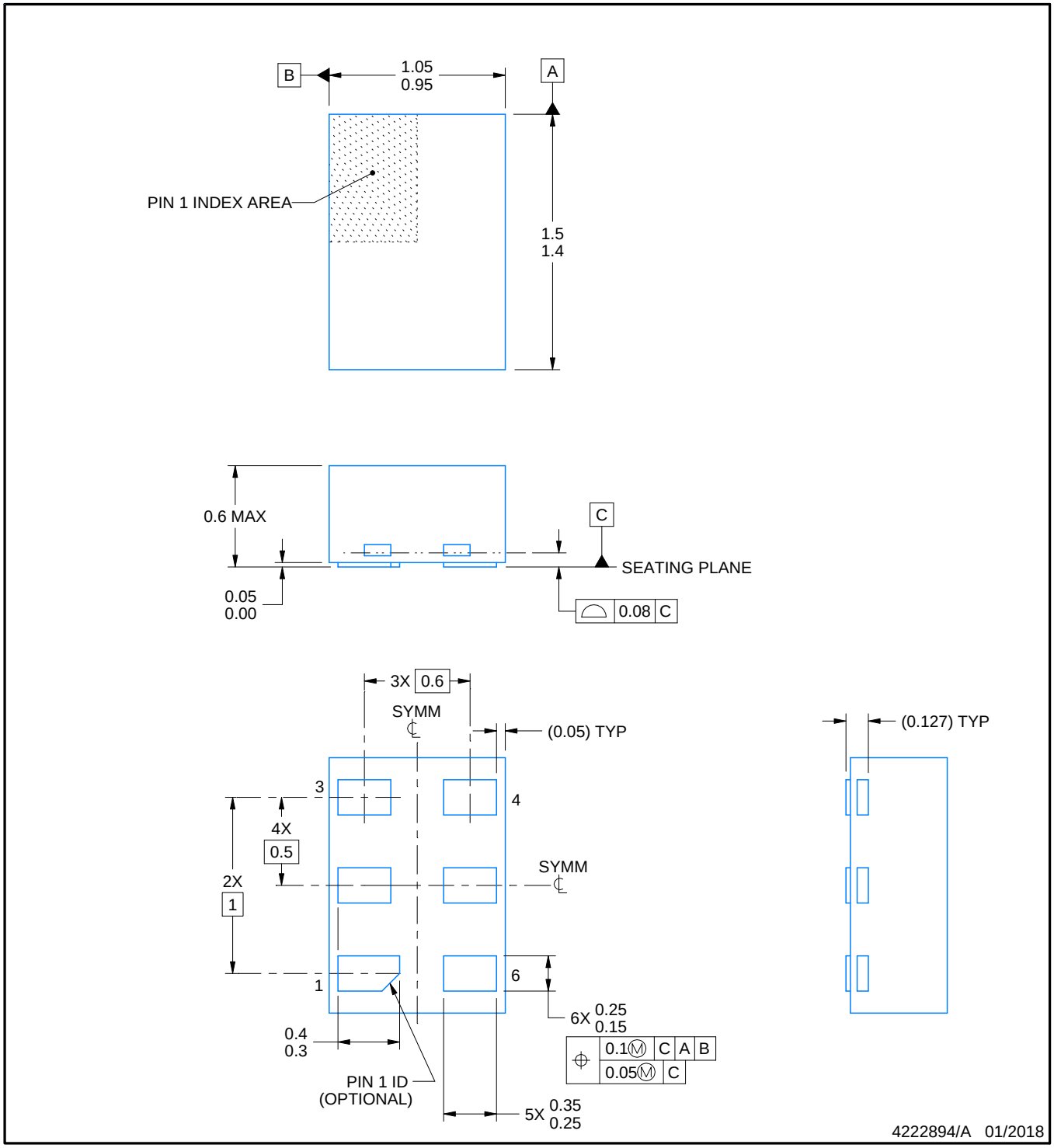
DRY0006A



PACKAGE OUTLINE

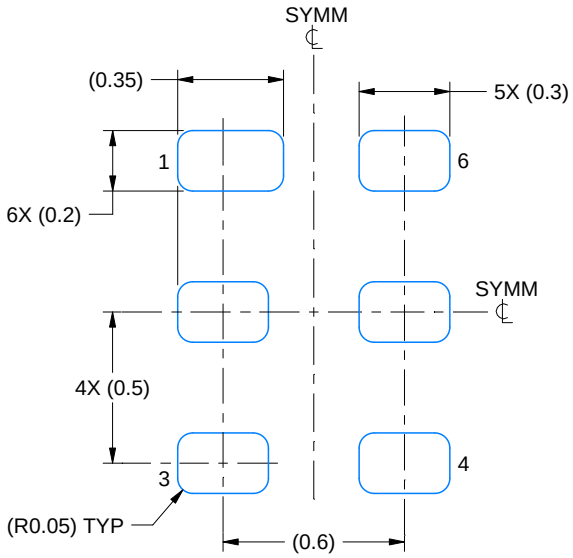
USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

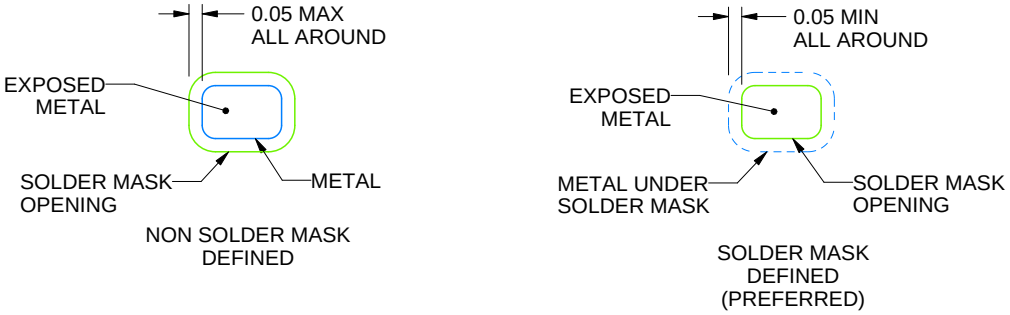


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
1:1 RATIO WITH PKG SOLDER PADS
EXPOSED METAL SHOWN
SCALE:40X



SOLDER MASK DETAILS

4222894/A 01/2018

NOTES: (continued)

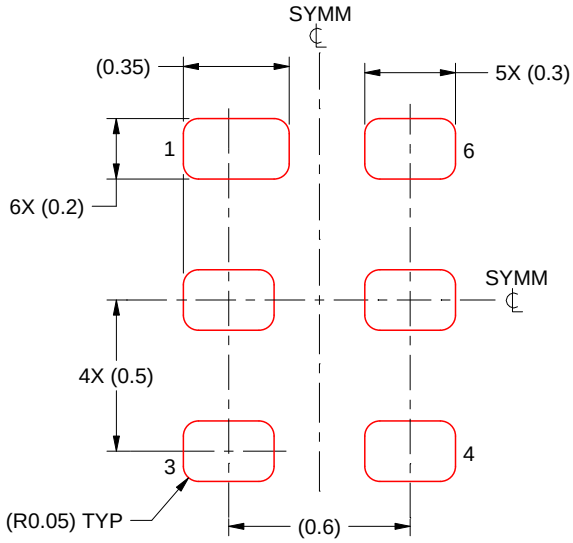
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).

EXAMPLE STENCIL DESIGN

DRY0006A

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



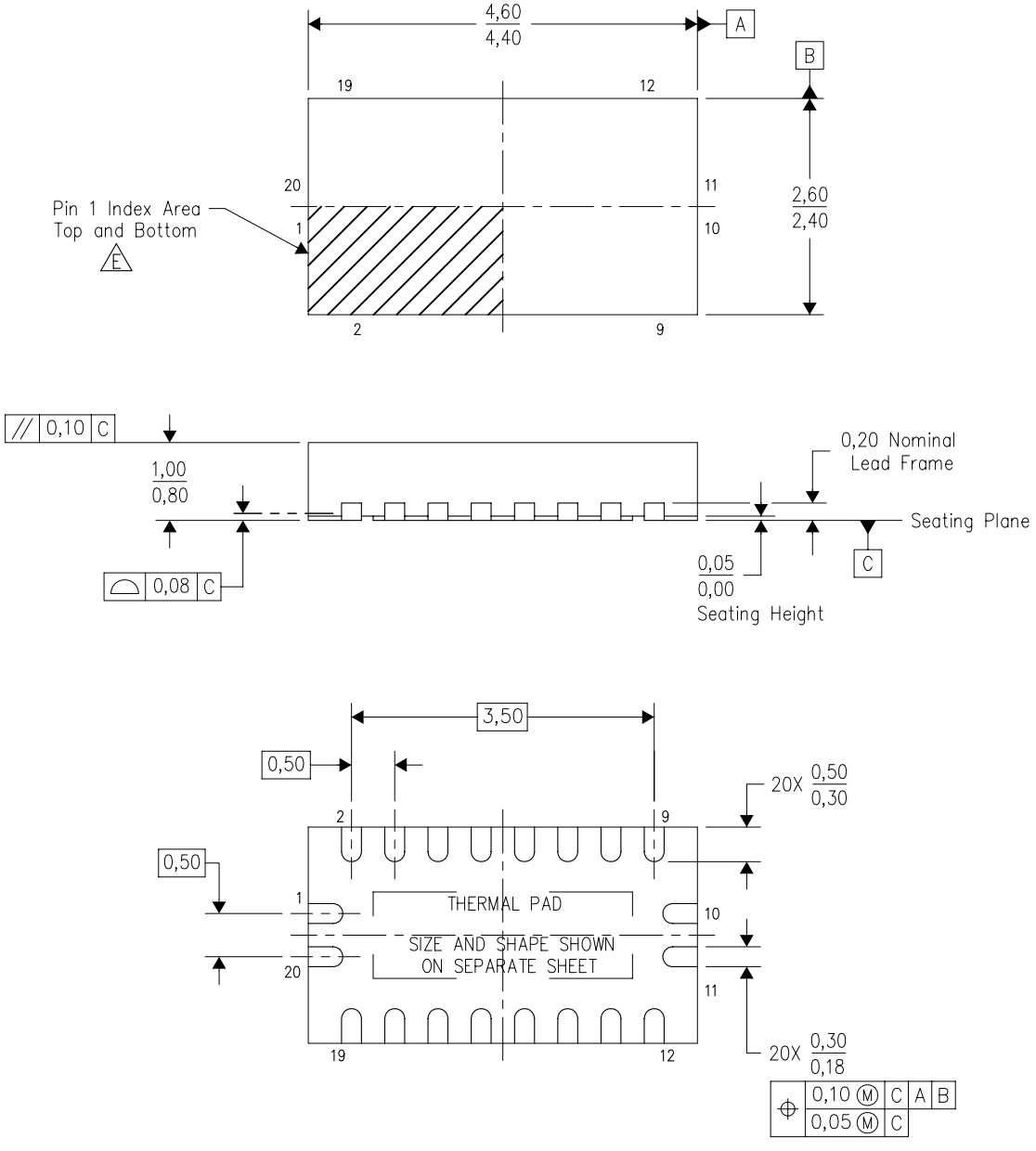
SOLDER PASTE EXAMPLE
BASED ON 0.075 - 0.1 mm THICK STENCIL
SCALE:40X

4222894/A 01/2018

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

RKS (R–PVQFN–N20) PLASTIC QUAD FLATPACK NO–LEAD



4211377/B 01/12

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No–Lead) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.

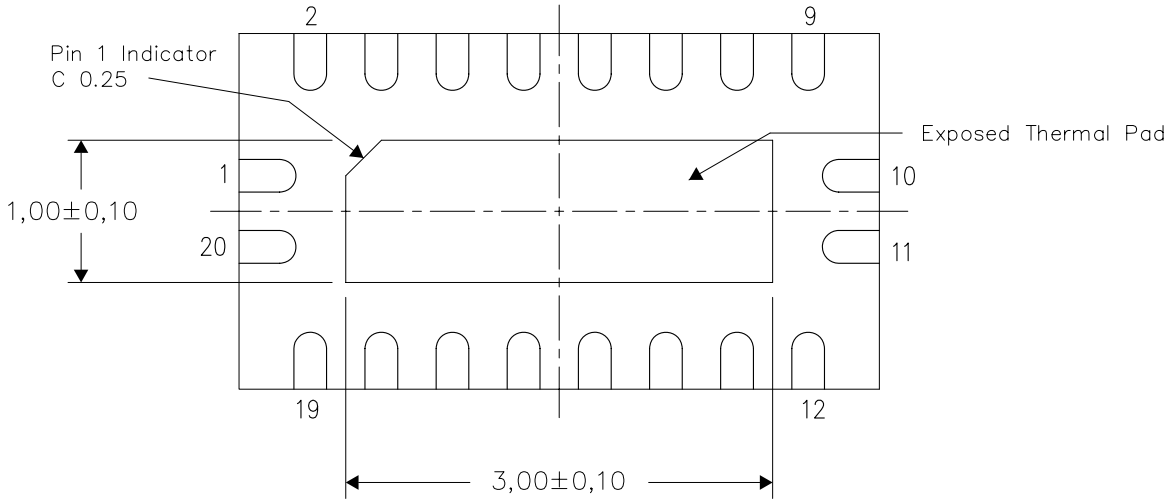
RKS (R–PVQFN–N20) PLASTIC QUAD FLATPACK NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



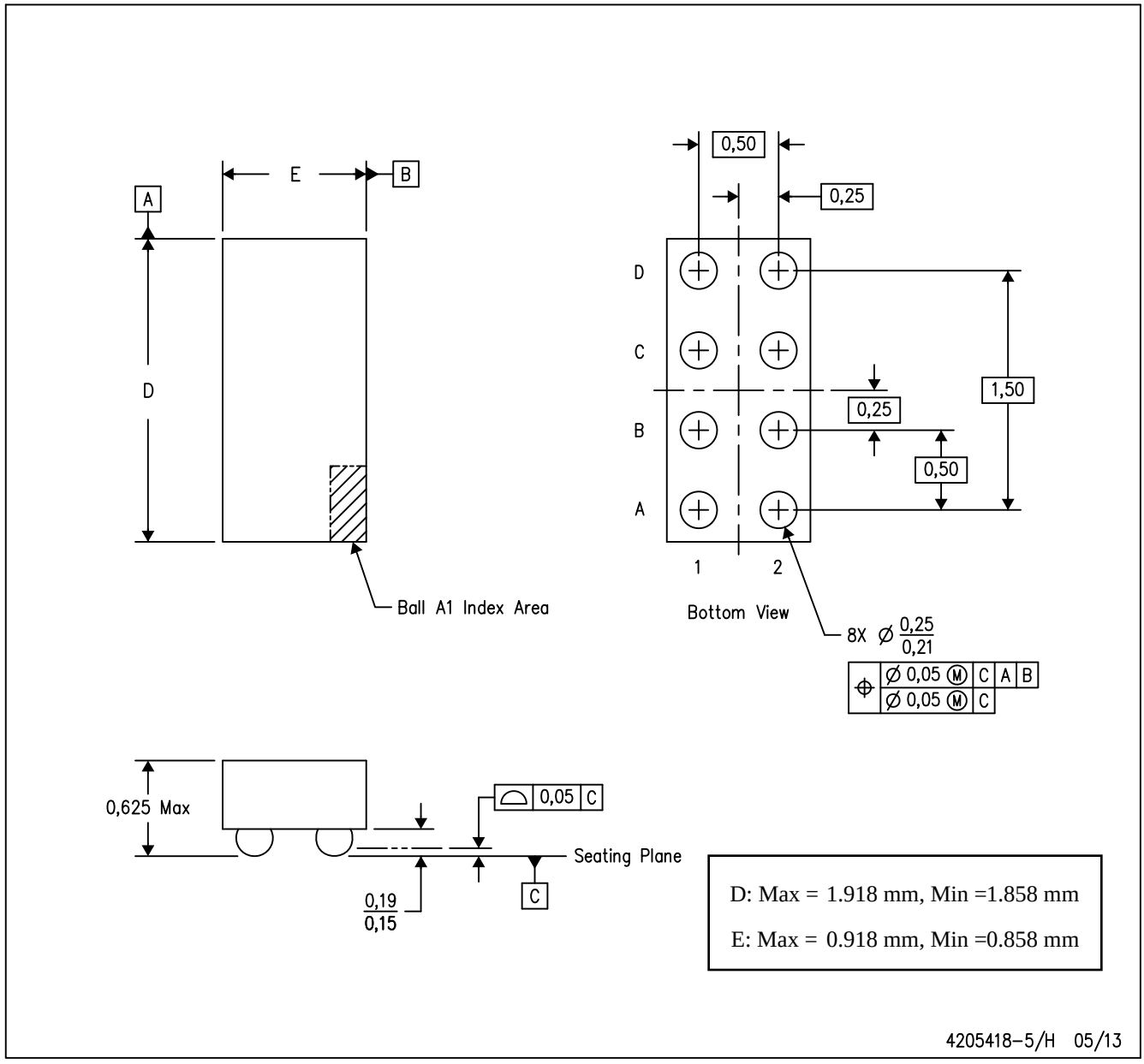
Bottom View

Exposed Thermal Pad Dimensions

4211394/B 01/12

NOTE: All linear dimensions are in millimeters

YZT (R–XBGA–N8) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.

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